Complementary Silicon Plastic Power Transistors

DPAK-3 for Surface Mount Applications

Designed for low voltage, low-power, high-gain audio amplifier applications.

Features

- High DC Current Gain
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Low Collector-Emitter Saturation Voltage
- High Current-Gain Bandwidth Product
- Annular Construction for Low Leakage
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|-----------|
| Collector-Base Voltage | V _{CB} | 100 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 100 | Vdc |
| Emitter-Base Voltage | V _{EB} | 7.0 | Vdc |
| Collector Current – Continuous | I _C | 4.0 | Adc |
| Collector Current – Peak | I _{CM} | 8.0 | Adc |
| Base Current | Ι _Β | 1.0 | Adc |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 12.5 0.1 | W W/°C |
| Total Device Dissipation @ T _A = 25°C (Note 2) Derate above 25°C | P _D | 1.4 0.011 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |
| ESD – Human Body Model | HBM | 3B | V |
| ESD – Machine Model | MM | С | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted on minimum pad sizes recommended.

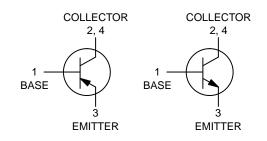


ON Semiconductor®

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4.0 A, 100 V, 12.5 W POWER TRANSISTOR

COMPLEMENTARY



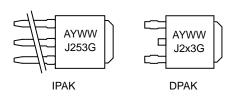


1 2 3

IPAK CASE 369D STYLE 1

DPAK-3 CASE 369C STYLE 1

MARKING DIAGRAMS



A = Assembly Location

Y = Year WW = Work Week x = 4 or 5

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|--------------------------------------|------------|------|
| Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 2) | R _{θJC} R _{θJA} | 10 89.3 | °C/W |

^{2.} When surface mounted on minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|-----------------------|----------|------------|--------------|
| OFF CHARACTERISTICS | <u> </u> | | • | |
| Collector–Emitter Sustaining Voltage (Note 3) (I _C = 10 mAdc, I _B = 0) | V _{CEO(sus)} | 100 | - | Vdc |
| Collector Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_J = 125^{\circ}\text{C})$ | І _{СВО} | - - | 100 100 | nAdc μAdc |
| Emitter Cutoff Current ($V_{BE} = 7.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | - | 100 | nAdc |
| DC Current Gain (Note 3) (I _C = 200 mAdc, V _{CE} = 1.0 Vdc) (I _C = 1.0 Adc, V _{CE} = 1.0 Vdc) | h _{FE} | 40 15 | 180 - | - |
| Collector–Emitter Saturation Voltage (Note 3) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$) | V _{CE(sat)} | <u>-</u> | 0.3 0.6 | Vdc |
| Base–Emitter Saturation Voltage (Note 3) (I _C = 2.0 Adc, I _B = 200 mAdc) | V _{BE(sat)} | - | 1.8 | Vdc |
| Base–Emitter On Voltage (Note 3) (I _C = 500 mAdc, V _{CE} = 1.0 Vdc) | V _{BE(on)} | - | 1.5 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Current–Gain – Bandwidth Product (Note 4) (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz) | f _T | 40 | - | MHz |
| Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$) | C _{ob} | - | 50 | pF |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \approx 2%. 4. f_T = |h_{FE}| • f_{test}.

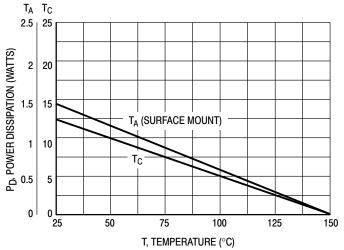


Figure 1. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

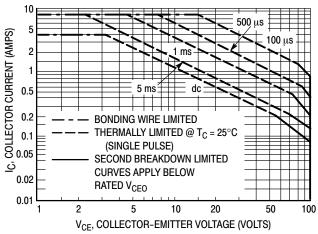


Figure 2. Active Region Maximum Safe Operating Area

The data of Figure 2 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

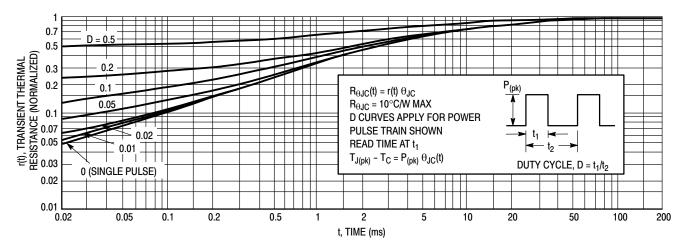


Figure 3. Thermal Response

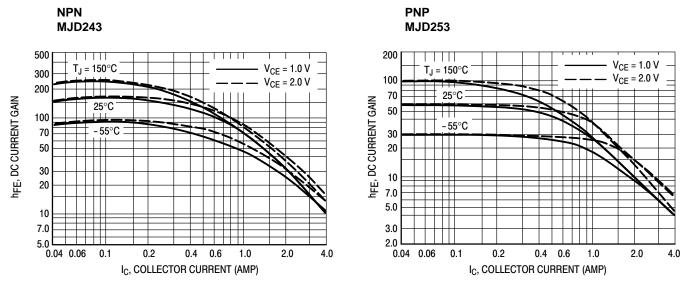


Figure 4. DC Current Gain

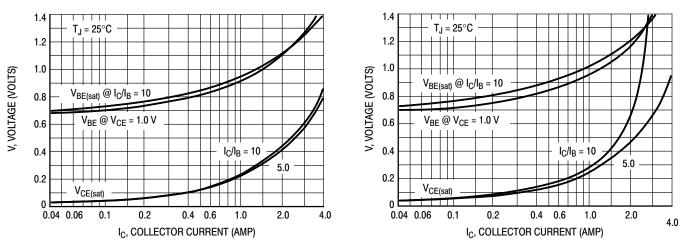


Figure 5. "On" Voltages

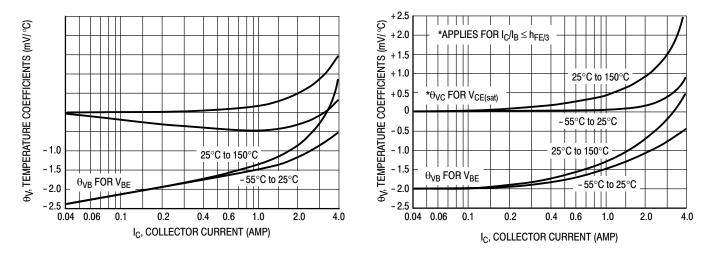
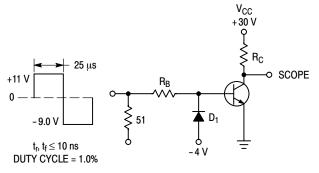


Figure 6. Temperature Coefficients



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D_1 MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE $I_B\approx 100$ mA MSD6100 USED BELOW $I_B\approx 100$ mA FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES

1K 500 300 200 100 t, TIME (ns) 50 30 20 10 $I_C/I_B = 10$ $T_J = 25^{\circ}C$ NPN MJD243 3 2 PNP MJD253 0.01 0.02 0.03 0.05 0.1 0.2 0.3 0.5 10 I_C, COLLECTOR CURRENT (AMPS)

Figure 8. Turn-On Time

Figure 7. Switching Time Test Circuit

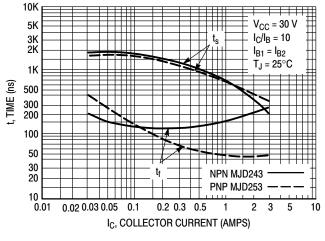


Figure 9. Turn-Off Time

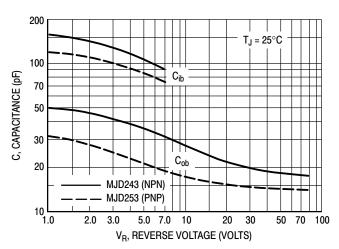


Figure 10. Capacitance

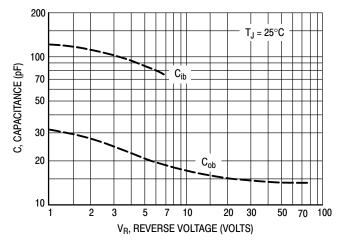


Figure 11. Capacitance

ORDERING INFORMATION

| Device | Package Type | Package | Shipping [†] |
|---------------|---------------------|---------|-----------------------|
| MJD243G | DPAK-3 (Pb-Free) | 369C | 75 Units / Rail |
| MJD243T4G | DPAK-3 (Pb-Free) | 369C | 2,500 / Tape & Reel |
| NJVMJD243T4G* | DPAK-3 (Pb-Free) | 369C | 2,500 / Tape & Reel |
| MJD253-1G | IPAK (Pb–Free) | 369D | 75 Units / Rail |
| MJD253T4G | DPAK-3 (Pb-Free) | 369C | 2,500 / Tape & Reel |
| NJVMJD253T4G* | DPAK-3 (Pb-Free) | 369C | 2,500 / Tape & Reel |

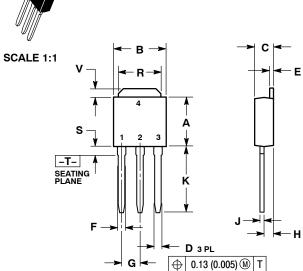
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

MECHANICAL CASE OUTLINE





DATE 15 DEC 2010



STYLE 2:

PIN 1. GATE

3

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

2. DRAIN

4. DRAIN

MT2

SOURCE

STYLE 1: PIN 1. BASE

3

STYLE 5: PIN 1. GATE

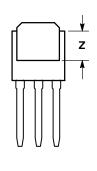
2. ANODE 3. CATHODE

ANODE

2. COLLECTOR

EMITTER

COLLECTOR



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS | |
|-----|--------|-------|----------|--------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.235 | 0.245 | 5.97 | 6.35 | |
| В | 0.250 | 0.265 | 6.35 | 6.73 | |
| С | 0.086 | 0.094 | 2.19 | 2.38 | |
| D | 0.027 | 0.035 | 0.69 | 0.88 | |
| E | 0.018 | 0.023 | 0.46 | 0.58 | |
| F | 0.037 | 0.045 | 0.94 | 1.14 | |
| G | 0.090 | BSC | 2.29 BSC | | |
| Н | 0.034 | 0.040 | 0.87 | 1.01 | |
| J | 0.018 | 0.023 | 0.46 | 0.58 | |
| K | 0.350 | 0.380 | 8.89 | 9.65 | |
| R | 0.180 | 0.215 | 4.45 | 5.45 | |
| S | 0.025 | 0.040 | 0.63 | 1.01 | |
| ٧ | 0.035 | 0.050 | 0.89 | 1.27 | |
| Z | 0.155 | | 3.93 | | |

MARKING DIAGRAMS

STYLE 3: PIN 1. ANODE

2. CATHODE

4. CATHODE

3 ANODE

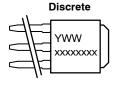
STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER

COLLECTOR

STYLE 4: PIN 1. CATHODE ANODE
 GATE

4. ANODE



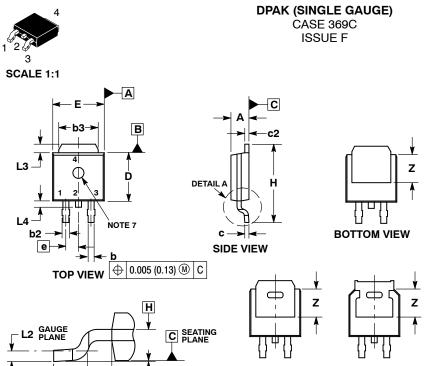


xxxxxxxxx = Device Code Α = Assembly Location IL = Wafer Lot Υ = Year WW = Work Week

| | | Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED | | |
|--|--------------|--|--|-------------|
| | DESCRIPTION: | IPAK (DPAK INSERTION MOUNT) | | PAGE 1 OF 1 |

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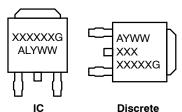
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

| | INCHES | | MILLIM | IETERS |
|-----|------------------------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.086 | 0.094 | 2.18 | 2.38 |
| A1 | 0.000 | 0.005 | 0.00 | 0.13 |
| b | 0.025 | 0.035 | 0.63 | 0.89 |
| b2 | 0.028 | 0.045 | 0.72 | 1.14 |
| b3 | 0.180 | 0.215 | 4.57 | 5.46 |
| С | 0.018 | 0.024 | 0.46 | 0.61 |
| c2 | 0.018 | 0.024 | 0.46 | 0.61 |
| D | 0.235 | 0.245 | 5.97 | 6.22 |
| E | 0.250 | 0.265 | 6.35 | 6.73 |
| е | 0.090 | BSC | 2.29 | BSC |
| Н | 0.370 | 0.410 | 9.40 | 10.41 |
| L | 0.055 | 0.070 | 1.40 | 1.78 |
| L1 | 0.114 REF 0.020 BSC | | 2.90 REF | |
| L2 | | | 0.51 BSC | |
| L3 | 0.035 | 0.050 | 0.89 | 1.27 |
| L4 | | 0.040 | | 1.01 |
| Z | 0.155 | | 3.93 | |

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code

= Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

SOLDERING FOOTPRINT*

STYLE 8:

STYLE 3:

PIN 1. N/C 2. CATHODE

3. ANODE 4. CATHODE

PIN 1. ANODE 2. CATHODE

3. ANODE

4. CATHODE

STYLE 9:

PIN 1. ANODE 2. CATHODE

Α1

STYLE 2:

PIN 1. GATE 2. COLLECTOR

3. EMITTER 4. COLLECTOR

PIN 1. GATE 2. DRAIN

SOURCE

4. DRAIN

DETAIL A ROTATED 90° CW

STYLE 7:

STYLE 1:

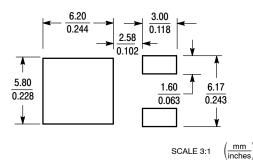
STYLE 6:

PIN 1. MT1 2. MT2

3. GATE 4. MT2

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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|------------------|---------------------|---|-------------|
| DESCRIPTION: | DPAK (SINGLE GAUGE) | | PAGE 1 OF 1 |

BOTTOM VIEW

ALTERNATE CONSTRUCTIONS

STYLE 5:

STYLE 10:

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE

PIN 1. CATHODE 2. ANODE

3. CATHODE 4. ANODE

STYLE 4:

PIN 1. CATHODE 2. ANODE 3. GATE

4. ANODE

3. RESISTOR ADJUST 4. CATHODE

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NJVMJD243T4G